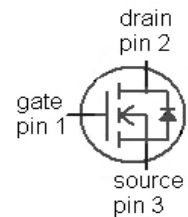
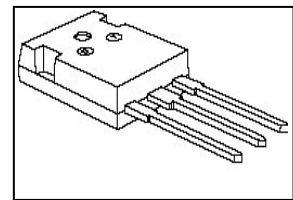


**CoolMOS™ Power Transistor**
**Features**

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme  $dv/dt$  rated
- Ultra low effective capacitances
- Improved transconductance

**Product Summary**

$V_{DS} @ T_{j,max}$	650	V
$R_{DS(on),max}$	0.1	$\Omega$
$I_D$	34.6	A

**P-TO247**


Type	Package	Ordering Code	Marking
SPW35N60C3	P-TO247	Q67040-S4673	35N60C3

**Maximum ratings, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25\text{ }^\circ\text{C}$	34.6	A
		$T_C=100\text{ }^\circ\text{C}$	21.9	
Pulsed drain current <sup>1)</sup>	$I_{D,pulse}$	$T_C=25\text{ }^\circ\text{C}$	103.8	
Avalanche energy, single pulse	$E_{AS}$	$I_D=17.3\text{ A}$ , $V_{DD}=50\text{ V}$	1500	mJ
Avalanche energy, repetitive $t_{AR}$ <sup>1),2)</sup>	$E_{AR}$	$I_D=34.6\text{ A}$ , $V_{DD}=50\text{ V}$	1.5	
Avalanche current, repetitive $t_{AR}$ <sup>1)</sup>	$I_{AR}$		34.6	A
Drain source voltage slope	$dv/dt$	$I_D=34.6\text{ A}$ , $V_{DS}=480\text{ V}$ , $T_j=125\text{ }^\circ\text{C}$	50	V/ns
Gate source voltage	$V_{GS}$	static	$\pm 20$	V
	$V_{GS}$	AC ( $f > 1\text{ Hz}$ )	$\pm 30$	
Power dissipation	$P_{tot}$	$T_C=25\text{ }^\circ\text{C}$	313	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 150	$^\circ\text{C}$

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Thermal characteristics</b>						
Thermal resistance, junction - case	$R_{thJC}$		-	-	0.4	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	leaded	-	-	62	
Soldering temperature	$T_{sold}$	1.6 mm (0.063 in.) from case for 10 s	-	-	260	°C

**Electrical characteristics, at  $T_j=25\text{ °C}$ , unless otherwise specified**

**Static characteristics**

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	600	-	-	V
Avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{ V}, I_D=34.6\text{ A}$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=1.9\text{ mA}$	2.1	3	3.9	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=600\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	0.1	1	$\mu\text{A}$
		$V_{DS}=600\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ °C}$	-	-	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=21.9\text{ A}, T_j=25\text{ °C}$	-	0.081	0.1	$\Omega$
		$V_{GS}=10\text{ V}, I_D=21.9\text{ A}, T_j=150\text{ °C}$	-	0.2	-	
Gate resistance	$R_G$	$f=1\text{ MHz}$ , open drain	-	0.6	-	
Transconductance	$g_{fs}$	$ V_{DS} >2 I_D R_{DS(on)max}, I_D=21.9\text{ A}$	-	36	-	S

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V}, f=1\text{ MHz}$	-	4500	-	pF
Output capacitance	$C_{oss}$		-	1500	-	
Reverse transfer capacitance	$C_{rss}$		-	100	-	
Effective output capacitance, energy related <sup>3)</sup>	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V	-	180	-	
Effective output capacitance, time related <sup>4)</sup>	$C_{o(tr)}$		-	324	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=480\text{ V}, V_{GS}=10\text{ V}, I_D=34.6\text{ A}, R_G=3.3\ \Omega$	-	10	-	ns
Rise time	$t_r$		-	5	-	
Turn-off delay time	$t_{d(off)}$		-	70	-	
Fall time	$t_f$		-	10	-	

**Gate Charge Characteristics**

Gate to source charge	$Q_{gs}$	$V_{DD}=480\text{ V}, I_D=34.6\text{ A}, V_{GS}=0\text{ to }10\text{ V}$	-	18	-	nC
Gate to drain charge	$Q_{gd}$		-	70	-	
Gate charge total	$Q_g$		-	150	200	
Gate plateau voltage	$V_{plateau}$		-	5.3	-	V

<sup>1)</sup> Pulse width limited by maximum temperature  $T_{j,max}$  only

<sup>2)</sup> Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV}=E_{AR} \cdot f$ .

<sup>3)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

<sup>4)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

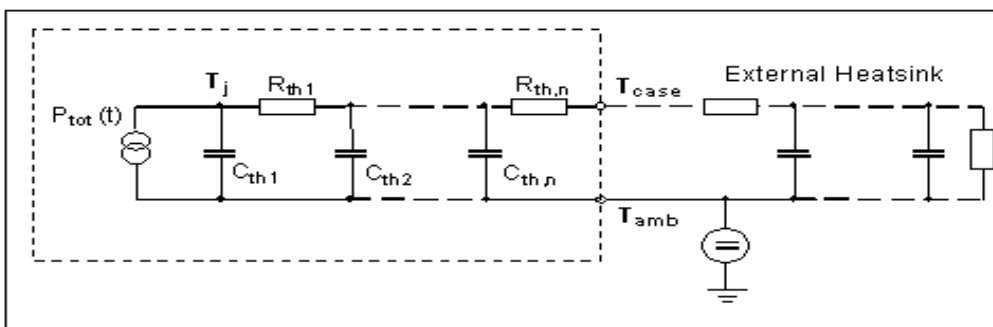
Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Reverse Diode**

Diode continuous forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	-	-	34.6	A
Diode pulse current	$I_{S,pulse}$		-	-	103.8	
Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=34.6\text{ A}, T_j=25\text{ }^\circ\text{C}$	-	0.95	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=480\text{ V}, I_F=I_S, di_F/dt=100\text{ A}/\mu\text{s}$	-	600	-	ns
Reverse recovery charge	$Q_{rr}$		-	21	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	90	-	A

**Typical Transient Thermal Characteristics**

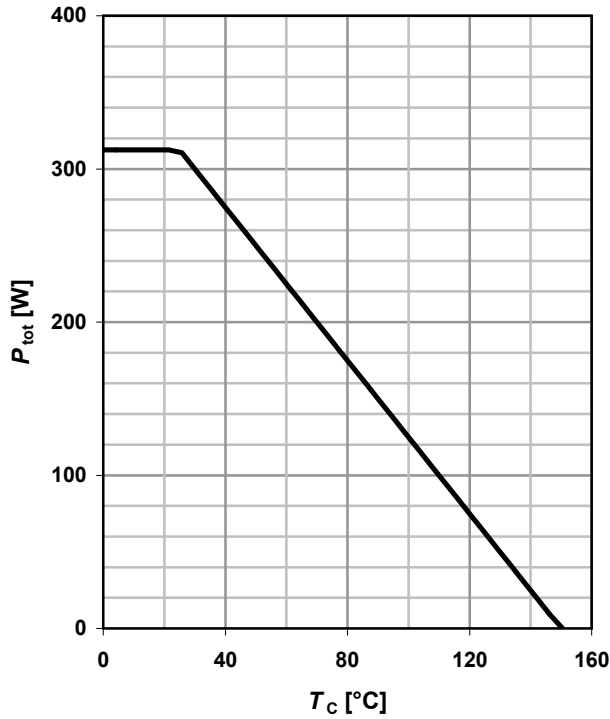
Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
$R_{th1}$	0.00441	K/W	$C_{th1}$	0.00037	Ws/K
$R_{th2}$	0.00608		$C_{th2}$	0.00223	
$R_{th3}$	0.0341		$C_{th3}$	0.00315	
$R_{th4}$	0.0602		$C_{th4}$	0.0179	
$R_{th5}$	0.0884		$C_{th5}$	0.098	
			$C_{th6}$	4.4 <sup>5)</sup>	



<sup>5)</sup>  $C_{th6}$  models the additional heat capacitance of the package in case of non-ideal cooling. It is not needed if  $R_{thCA}=0\text{ K/W}$ .

**1 Power dissipation**

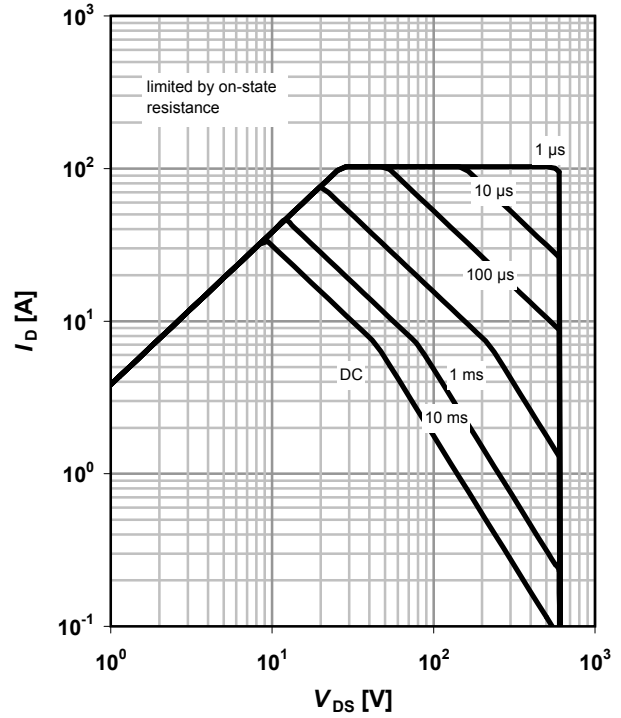
$P_{tot}=f(T_C)$



**2 Safe operating area**

$I_D=f(V_{DS}); T_C=25\text{ }^\circ\text{C}; D=0$

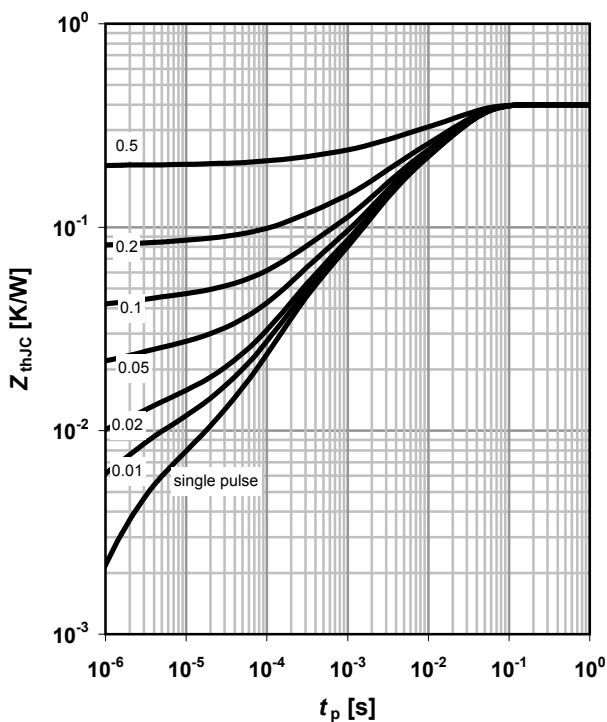
parameter:  $t_p$



**3 Max. transient thermal impedance**

$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C}$

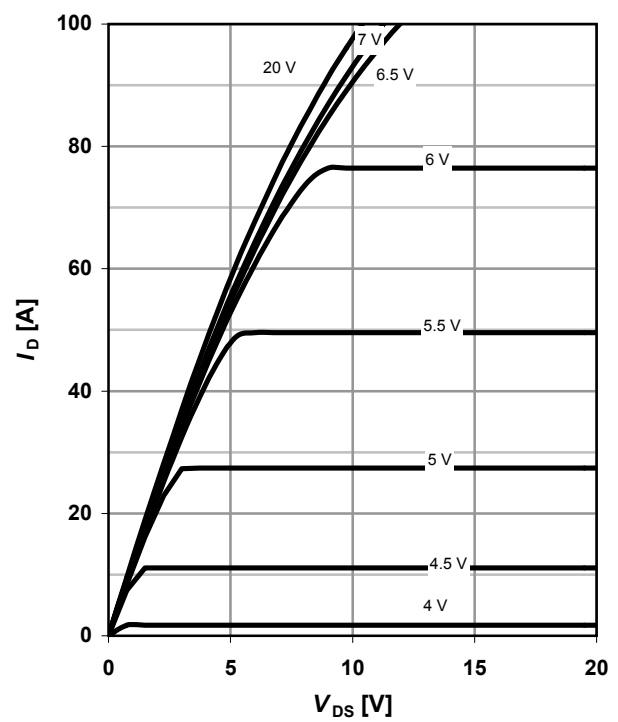
parameter:  $D=t_p/T$



**4 Typ. output characteristics**

$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C}$

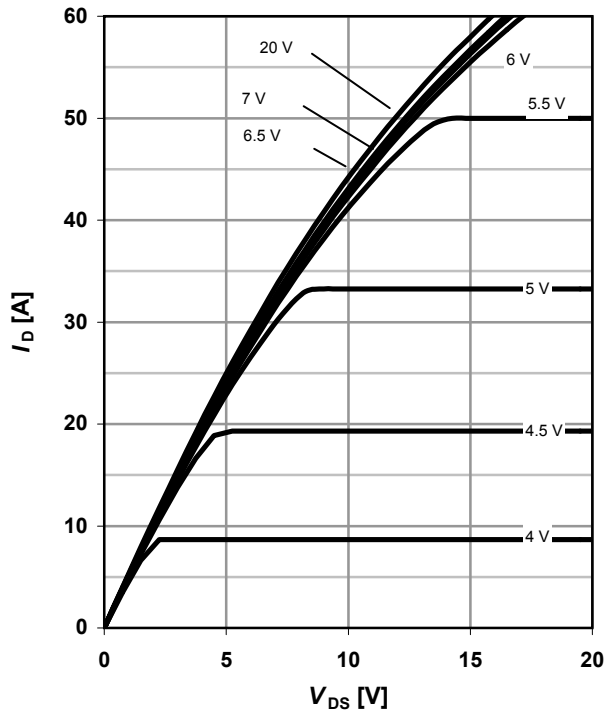
parameter:  $V_{GS}$



**5 Typ. output characteristics**

$I_D = f(V_{DS}); T_j = 150\text{ °C}$

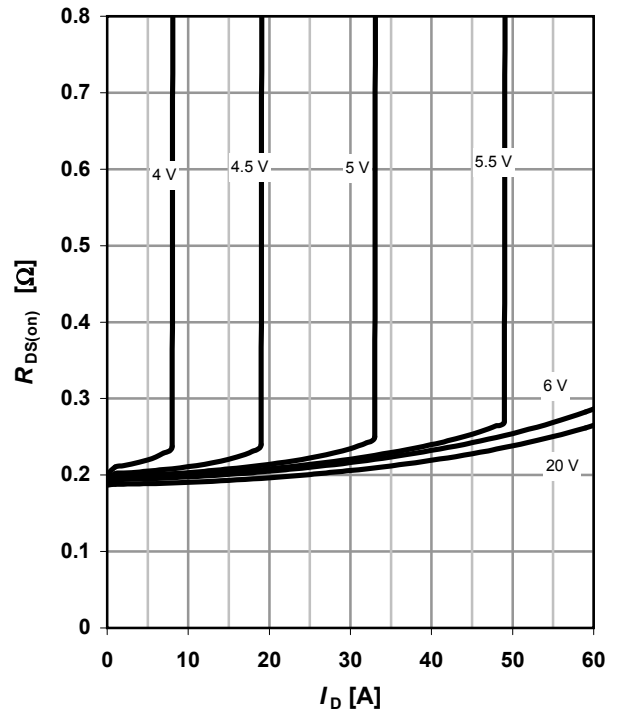
parameter:  $V_{GS}$



**6 Typ. drain-source on-state resistance**

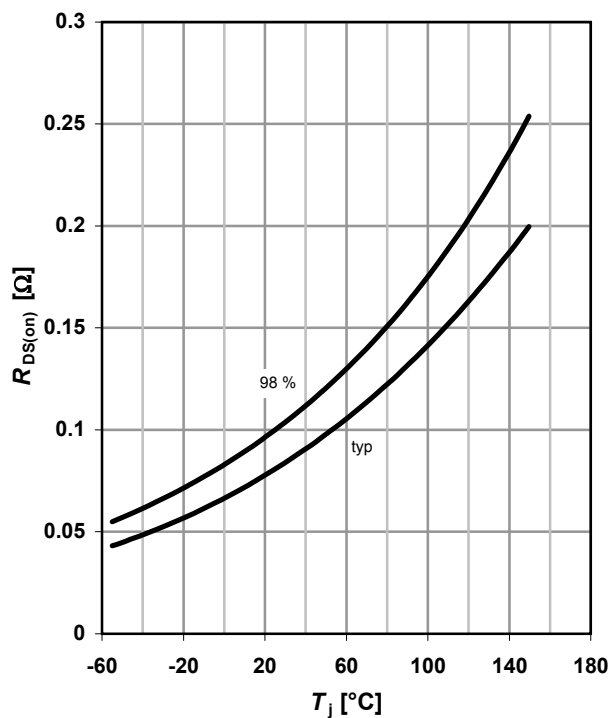
$R_{DS(on)} = f(I_D); T_j = 150\text{ °C}$

parameter:  $V_{GS}$



**7 Drain-source on-state resistance**

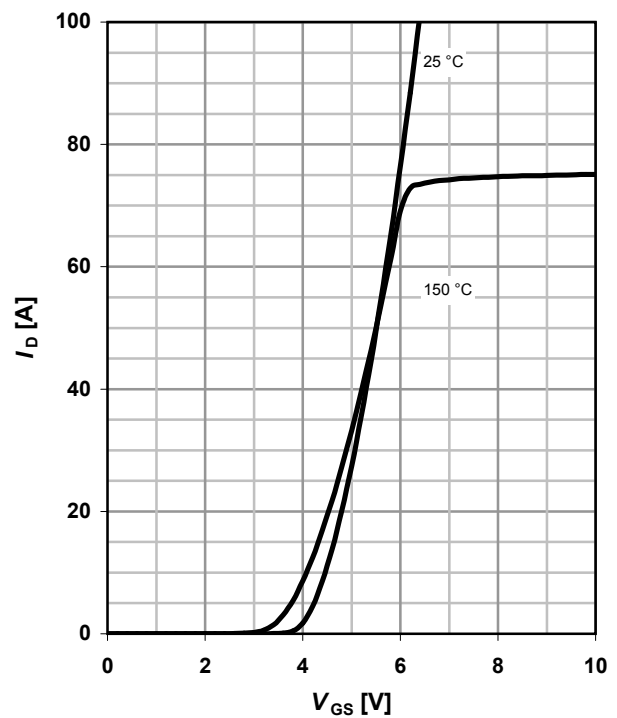
$R_{DS(on)} = f(T_j); I_D = 21.9\text{ A}; V_{GS} = 10\text{ V}$



**8 Typ. transfer characteristics**

$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

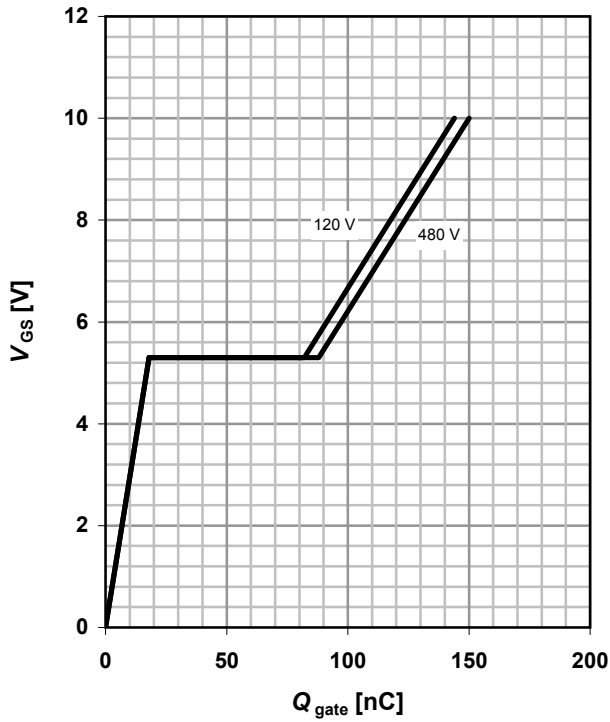
parameter:  $T_j$



**9 Typ. gate charge**

$V_{GS}=f(Q_{gate}); I_D=34.6 \text{ A pulsed}$

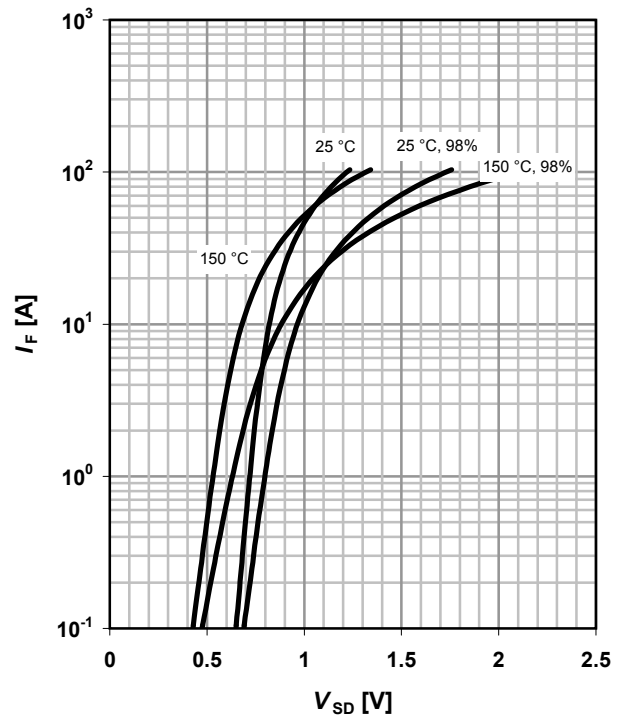
parameter:  $V_{DD}$



**10 Forward characteristics of reverse diode**

$I_F=f(V_{SD})$

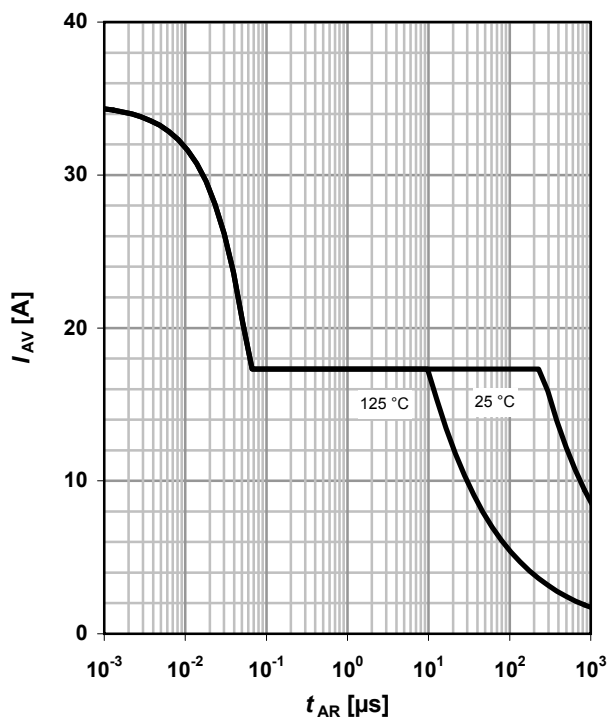
parameter:  $T_j$



**11 Avalanche SOA**

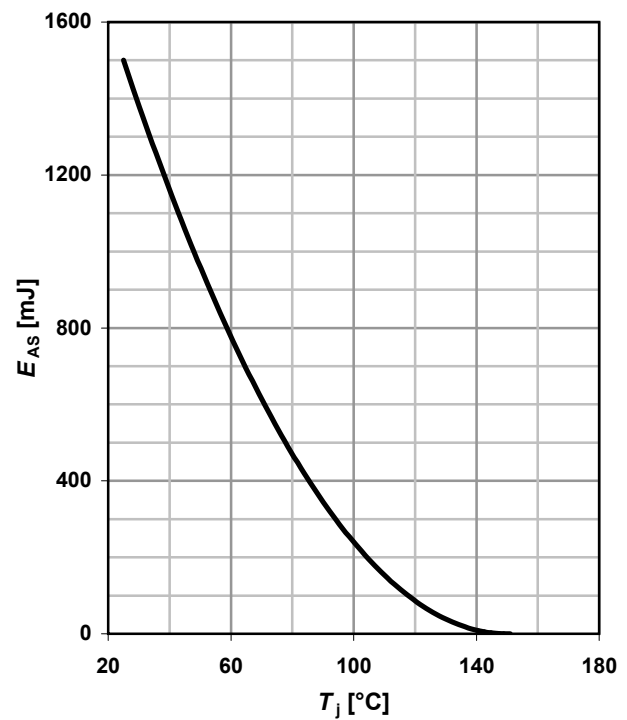
$I_{AR}=f(t_{AR})$

parameter:  $T_{j(start)}$



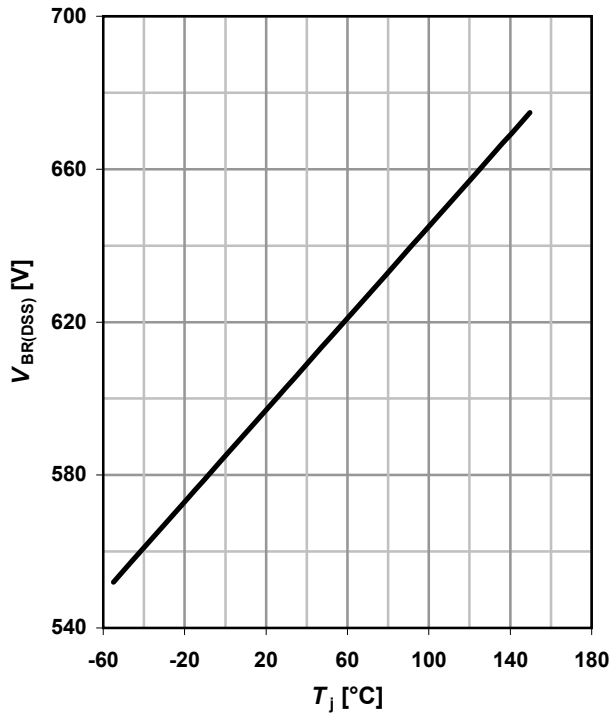
**12 Avalanche energy**

$E_{AS}=f(T_j); I_D=17.3 \text{ A}; V_{DD}=50 \text{ V}$



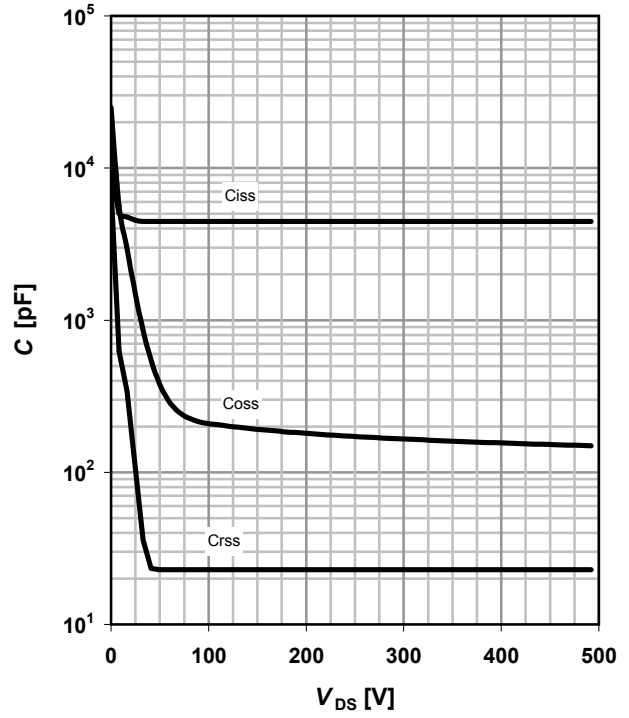
**13 Drain-source breakdown voltage**

$$V_{BR(DSS)} = f(T_j); I_D = 0.25 \text{ mA}$$



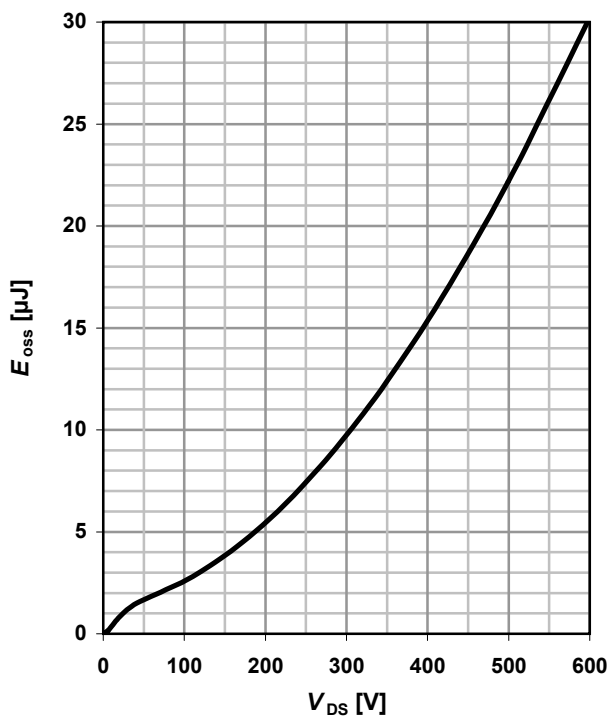
**14 Typ. capacitances**

$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



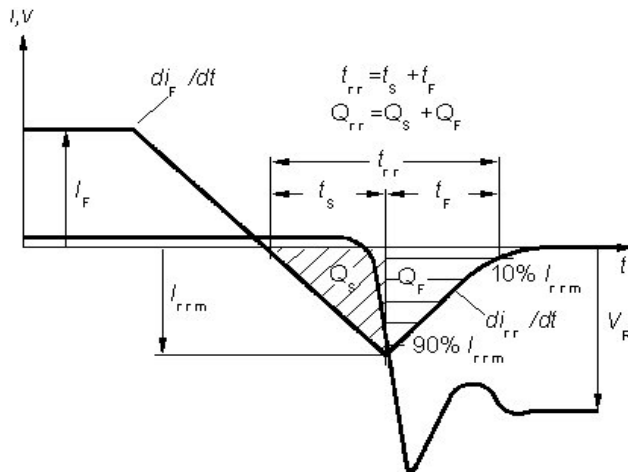
**15 Typ.  $C_{oss}$  stored energy**

$$E_{oss} = f(V_{DS})$$

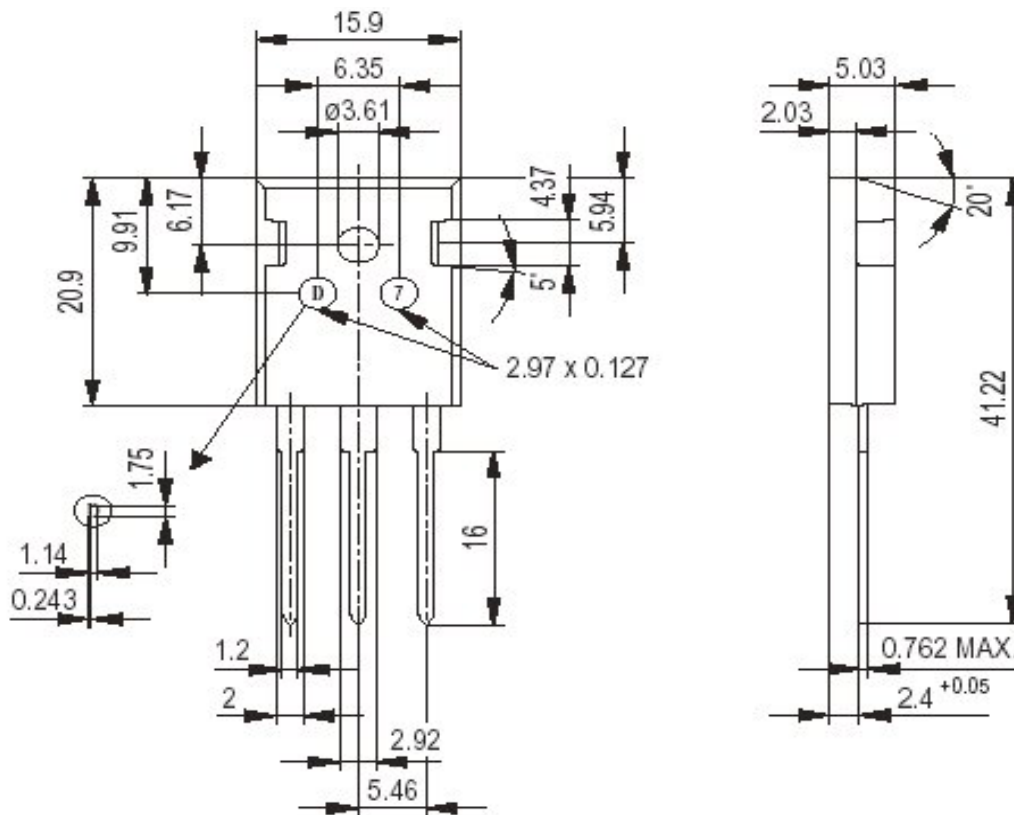




Definition of diode switching characteristics



P-TO247: Outline



General tolerance unless otherwise specified: Leadframe parts:  $\pm 0.05$   
 Package parts:  $\pm 0.12$

Dimensions in mm

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